Recording of cell action potentials with AlGaN/GaN field-effect transistors

Georg Steinhoff and Barbara Baur
Walter Schottky Institut, Technische Universität München, Am Coulombwall 3, D-85748 Garching, Germany

Günter Wrobel, Sven Ingebrandt, and Andreas Offenhäusser
Institut für Schichten und Grenzflächen ISG-2, Forschungszentrum Jülich, Leo-Brandt-Straße, D-52428 Jülich, Germany

Armin Dadgar and Alois Krost
Otto-von-Guericke Universität Magdeburg, Abteilung Halbleiterepitaxie, Postfach 4120, D-39016 Magdeburg, Germany

Martin Stutzmann and Martin Eickhoff
Walter Schottky Institut, Technische Universität München, Am Coulombwall 3, D-85748 Garching, Germany (Received 13 September 2004; accepted 23 November 2004; published online 12 January 2005)

An AlGaN/GaN electrolyte gate field-effect transistor array for the detection of electrical cell signals has been realized. The low-frequency noise power spectral density of these devices exhibits a 1/f characteristic with a dimensionless Hooge parameter of $5 \times 10^{-3}$. The equivalent gate-input noise under operation conditions has a peak-to-peak amplitude of $15 \mu V$, one order of magnitude smaller than for common silicon-based devices used for extracellular recordings. Extracellular action potentials from a confluent layer of rat heart muscle cells cultivated directly on the nonmetallized gate surface were recorded with a signal amplitude of $75 \mu V$ and a signal-to-noise ratio of 5:1. © 2005 American Institute of Physics. [DOI: 10.1063/1.1853531]

Recording of electrical activity of cells with planar device arrays is a promising approach for the study of biological networks as well as for the realization of whole-cell biosensors, in which cultured cells act as the biological receptor unit. Such hybrid sensors benefit from the high sensitivity and selectivity of the specific receptors in the cellular membrane and the signal amplification in second messenger pathways of the cells. These cell-sensor hybrids are suitable for a variety of applications, such as drug discovery and screening in pharmacology, detection of toxins, and environmental monitoring. Most of these applications require a noninvasive multisite recording system suitable for long-term measurements under physiological conditions. This excludes the utilization of conventional invasive patch-clamp techniques or voltage-sensitive dyes, which are toxic on illumination.

Extracellular monitoring of electrical cell activity can be performed by microelectrode arrays or field-effect transistor (FET) device arrays, as first reported for muscle fibers and neuronal slices. Silicon-based electrolyte oxide FETs are generally used as transducers for this purpose. The main drawbacks of these devices are their long-term drift in electrolytes due to the electrochemical instability of the SiO$_2$ surface and a high noise level due to mobility fluctuations caused by trapping and detrapping of carriers to and from trap states at the interface to the gate oxide layer. Therefore, alternative concepts such as buried-channel FETs and floating-gate devices have been developed.

Another approach is the application of alternative material systems for the realization of electrolyte-gate FETs (EGFETs) such as AlGaN/GaN heterostructure FETs. Group III-nitrides are chemically stable under physiological conditions and nontoxic to living cells and AlGaN/GaN FETs have recently been demonstrated to exhibit promising properties for sensor applications in liquid and electrolyte environments.

Here, we report the recording of electrical signals from a cardiac myocyte syncytium cultivated on the surface of AlGaN/GaN heterostructure EGFET arrays.

Transistor arrays consisting of 4 x 4 individual devices were processed on AlGaN/GaN heterostructures grown by metalorganic vapor phase epitaxy on sapphire substrates. The heterostructures consisted of a 24–26 nm undoped AlGaN barrier and a 3 nm undoped GaN cap, grown on a 1.5 μm GaN buffer. For some devices, the GaN buffer was compensated by Fe doping. The Al content in the AlGaN barriers was between 20% and 30%, as determined by high-resolution x-ray diffraction measurements.

The preparation for the cardiac myocyte cells of embryonic Wistar rats (Charles River GmbH, Sulzbach, Germany) was adapted from previously published protocols. The AlGaN/GaN chips were cleaned with 70% (v/v) ethanol (p.a.) and coated for 30 min with 20 μl of 12.5 μg/ml fibronectin (Sigma-Aldrich) in Hanks’ balanced salt solution (HBSS) at 37 °C. The surfaces were rinsed with Phosphate-buffered saline (PBS) buffer solution (137 mM NaCl, 2.7 mM KCl, 4.3 mM Na$_2$HPO$_4$, 1.4 mM NaH$_2$PO$_4$, pH 7.3). The cells were then plated onto the chips at densities of 3000–5000 cells/mm$^2$ exposed chip area (effective chip surface: 6.2 mm$^2$). The chips were kept at 37 °C and 5% CO$_2$. The recording of cell action potentials with AlGaN/GaN field-effect transistors

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in a humidified chamber. The Ham’s F10 medium (Sigma-Aldrich) containing 5% (v/v) foetal bovine serum (FBS), 1% (v/v) penicillin-streptomycin (10 000 units/ml penicillin and 10 mg/ml streptomycin, Sigma-Aldrich) and 0.5% (v/v) insulin/transferrin/selenium (ITS) (Sigma-Aldrich), adjusted to pH 7.2 was replaced several times. After 5 to 6 days in culture a confluent monolayer of cells (syncytium) developed, which spontaneously contracted with stable frequency and the electrical signals of the cells were recorded. Therefore, the culture medium was replaced by extracellular solution (145 mM NaCl, 3 mM KCl, 2 mM MgCl$_2$, 3 mM CaCl$_2$, 10 mM N-2–Hydroxyethylpiperazine-N’$^\text{8}$-2–ethanesulfonic acid (HEPES), 8 mM glucose, adjusted to pH 7.3 with NaOH). Figure 1 shows cardiac myocyte cells on the gates of the AlGaN/GaN transistors.

For electrical measurements, the potential of the electrolytic gate of the devices was defined by an Ag/AgCl-wire reference electrode, which was connected to ground potential. As cell action potentials occur at low frequencies, a low-pass filter at 3 kHz was used to reduce the noise level during signal recording. Figure 2 shows the transconductance of a single AlGaN/GaN-EGFET element as a function of the gate-source voltage ($V_{GS}$). Under usual operating conditions (drain-source voltage $V_{DS}=0.5$ V), the devices exhibited a maximum transconductance $g_m$ of 0.2 mS at $V_{GS}=-1.8$ V. Under these conditions, the leakage current $I_{GS}$ through the electrolytic gate was found to be negligible (<2 nA).

Low-frequency noise (1 Hz< $f$< 1 kHz) was measured in the common source configuration for different gate-source voltages at room temperature. From the observed drain-source current noise, the equivalent gate-input noise was calculated by $S_{VGS}=S_{IGS}/g_m^2$. Figure 3(a) displays a typical noise power density spectrum, which shows a $1/f$ frequency dependence. The exponent $\gamma$ varies with $V_{GS}$ between $\gamma=0.9$ and 1.3. The corresponding dimensionless Hooge parameter $\alpha$ (Ref. 23) was calculated to be $5 \times 10^{-3}$ at $V_{GS}=0$ V from the relative source-drain current spectral density $S_{IDS}/I_{DS}^2$. The noise power spectral density exhibits a minimum for $V_{GS}=-1.8$ V, as shown in Fig. 3(b) for different frequencies. The equivalent gate-source voltage noise under these conditions presents a peak-to-peak amplitude of 15 $\mu$V, which is one order of magnitude smaller than for comparable silicon-based devices.\textsuperscript{12,24}

The high signal-to-noise (S/N) ratio of our AlGaN/GaN EGFET device is demonstrated in Fig. 4, which presents the change in equivalent gate-source voltage calculated from the
change in the source-drain current upon application of a 100 \( \mu \text{V} \) test pulse to the electrolyte gate for a time interval of 100 ms. The signal is clearly resolved on the background noise with a S/N ratio of \( >5:1 \).

In Fig. 5, recordings of a spontaneously beating cardiac myocyte synchytium cultivated on the device surface are shown. The voltage \( V_J \) in the junction area between cell and transistor gate was recorded. Transistor signals were 100–150 ms in duration, firing at a stable frequency for several minutes. Signals with an amplitude of 70 \( \mu \text{V} \) were clearly detected because of the low background noise of the AlGaN/GaN transistors.

Action potentials of electrogenic cells are generated mainly by ionic fluxes of sodium, calcium, and potassium across the cellular membrane. The initial event is an influx of sodium ions, triggering a fast-rising action potential. In the case of cardiac myocytes, the action potential is retarded by an inward directed calcium flux leading to a plateau phase. The following potassium efflux leads to a repolarization of the cell. The shape of the action potentials recorded with planar sensors can be described in first approximation by a point-contact model, which considers mainly two contributions to the electrical signal: capacitive currents across the attached part of the cellular membrane into the contact point caused by changes of the intracellular potential, and, ionic currents through ion channels in the attached membrane part, which are forced to flow along a small cleft formed by the cellular membrane and the sensor surface acting as an electrical resistor. Both currents lead to a voltage change at the sensor surface and have to be summed for the interpretation of the recorded signal shape.

The signal shapes recorded by the AlGaN/GaN transistors (Fig. 5) seem to consist mainly out of the potassium signal part. The exact reason for this signal shape remains to be clarified.

In conclusion, the recording of the spontaneous extracellular action potentials with AlGaN/GaN EGFET arrays has been demonstrated. The devices show stable operation under physiological conditions and, due to the low noise, a much higher signal resolution than currently used Si-based devices.

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\[ \text{FIG. 5. Extracellular potential of a spontaneously beating cardiac myocyte synchytium recorded with an AlGaN/GaN EGFET. The cells were cultivated on the device surface.} \]